

Edith Bellet-Amalric

List of Publications by Year in descending order

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121
all docs

121
docs citations

121
times ranked

3184
citing authors

#	ARTICLE	IF	CITATIONS
1	Regulated Dynamics with Two Monolayer Steps in Vapor-Solid Growth of Nanowires. ACS Nano, 2022, 16, 4397-4407.	14.6	5
2	The onset of tapering in the early stage of growth of a nanowire. Nanotechnology, 2022, 33, 255601.	2.6	2
3	A high throughput study of both compositionally graded and homogeneous Fe-Pt thin films. Journal of Materials Research and Technology, 2022, 18, 1245-1255.	5.8	3
4	200 mm-scale growth of 2D layered GaSe with preferential orientation. APL Materials, 2022, 10, 051106.	5.1	1
5	Solubility Limit of Ge Dopants in AlGaIn: A Chemical and Microstructural Investigation Down to the Nanoscale. ACS Applied Materials & Interfaces, 2021, 13, 4165-4173.	8.0	7
6	AlGaIn/GaN asymmetric graded-index separate confinement heterostructures designed for electron-beam pumped UV lasers. Optics Express, 2021, 29, 13084.	3.4	5
7	Design of AlGaIn/AlN Dot-in-Wire Heterostructures for Electron-Pumped UV Emitters. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1900714.	1.8	4
8	Controlling the shape of a tapered nanowire: lessons from the Burton-Cabrera-Frank model. Nanotechnology, 2020, 31, 274004.	2.6	3
9	Radio-frequency stress-induced modulation of CdTe/ZnTe quantum dots. Journal of Applied Physics, 2020, 127, .	2.5	2
10	Achieving visible light-driven hydrogen evolution at positive bias with a hybrid copper-iron oxide TiO ₂ -cobaloxime photocathode. Green Chemistry, 2020, 22, 3141-3149.	9.0	9
11	Assessment of AlGaIn/AlN superlattices on GaN nanowires as active region of electron-pumped ultraviolet sources. Nanotechnology, 2020, 31, 204001.	2.6	14
12	Internal quantum efficiency of AlGaIn/AlN quantum dot superlattices for electron-pumped ultraviolet sources. Nanotechnology, 2020, 31, 505205.	2.6	6
13	Three-phase metal-insulator transition and structural alternative for a VO ₂ film epitaxially grown on Al ₂ O ₃ (0001). Journal of Applied Physics, 2019, 126, 165306.	2.5	5
14	Probing the light hole/heavy hole switching with correlated magneto-optical spectroscopy and chemical analysis on a single quantum dot. Nanotechnology, 2019, 30, 175301.	2.6	2
15	On intrinsic Stokes shift in wide GaN/AlGaIn polar quantum wells. Semiconductor Science and Technology, 2019, 34, 075021.	2.0	1
16	Near- and mid-infrared intersubband absorption in top-down GaN/AlIn nano- and micro-pillars. Nanotechnology, 2019, 30, 054002.	2.6	5
17	Nanowire growth and sublimation: CdTe quantum dots in ZnTe nanowires. Physical Review Materials, 2018, 2, .	2.4	9
18	Coupling Semiconducting Nanowires to Plasmonic Nanoantennas. NATO Science for Peace and Security Series B: Physics and Biophysics, 2017, , 517-518.	0.3	0

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19	Intersubband absorption in Si- and Ge-doped GaN/AlN heterostructures in self-assembled nanowire and 2D layers. <i>Physica Status Solidi (B): Basic Research</i> , 2017, 254, 1600734.	1.5	16
20	Light-hole exciton in a nanowire quantum dot. <i>Physical Review B</i> , 2017, 95, .	3.2	24
21	Effect of Al incorporation in nonpolar <i>m</i> -plane GaN/AlGaN multi-quantum-wells using plasma-assisted molecular-beam epitaxy. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2017, 214, 1600849.	1.8	6
22	Effect of doping on the intersubband absorption in Si- and Ge-doped GaN/AlN heterostructures. <i>Nanotechnology</i> , 2017, 28, 405204.	2.6	24
23	Enhanced Photon Extraction from a Nanowire Quantum Dot Using a Bottom-Up Photonic Shell. <i>Physical Review Applied</i> , 2017, 8, .	3.8	13
24	Control of the incubation time in the vapor-solid-solid growth of semiconductor nanowires. <i>Applied Physics Letters</i> , 2017, 110, 263107.	3.3	4
25	Highly uniform zinc blende GaAs nanowires on Si(111) using a controlled chemical oxide template. <i>Nanotechnology</i> , 2017, 28, 255602.	2.6	5
26	Diffusion-driven growth of nanowires by low-temperature molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	13
27	Short-wavelength, mid- and far-infrared intersubband absorption in nonpolar GaN/Al(Ga)N heterostructures. <i>Japanese Journal of Applied Physics</i> , 2016, 55, 05FG05.	1.5	9
28	Unraveling the strain state of GaN down to single nanowires. <i>Journal of Applied Physics</i> , 2016, 120, .	2.5	6
29	Deterministic radiative coupling between plasmonic nanoantennas and semiconducting nanowire quantum dots. <i>Nanotechnology</i> , 2016, 27, 185201.	2.6	3
30	Quantitative Reconstructions of 3D Chemical Nanostructures in Nanowires. <i>Nano Letters</i> , 2016, 16, 1637-1642.	9.1	30
31	Effect of doping on the far-infrared intersubband transitions in nonpolar <i>m</i> -plane GaN/AlGaN heterostructures. <i>Nanotechnology</i> , 2016, 27, 145201.	2.6	16
32	Intersubband transitions in nonpolar GaN/Al(Ga)N heterostructures in the short- and mid-wavelength infrared regions. <i>Journal of Applied Physics</i> , 2015, 118, 014309.	2.5	26
33	High In-content InGaN layers synthesized by plasma-assisted molecular-beam epitaxy: Growth conditions, strain relaxation, and In incorporation kinetics. <i>Journal of Applied Physics</i> , 2014, 116, .	2.5	36
34	Boron-doped superlattices and Bragg mirrors in diamond. <i>Applied Physics Letters</i> , 2014, 105, 081109.	3.3	8
35	Bottom-up approach to control the photon outcoupling of a II-VI quantum dot with a photonic wire. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2014, 11, 1263-1266.	0.8	4
36	Enhanced room-temperature mid-ultraviolet emission from AlGaIn/AlN Stranski-Krastanov quantum dots. <i>Journal of Applied Physics</i> , 2014, 116, 023502.	2.5	14

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37	Pseudo-square AlGaIn/GaN quantum wells for terahertz absorption. Applied Physics Letters, 2014, 105, 131106.	3.3	25
38	Structure and Morphology in Diffusion-Driven Growth of Nanowires: The Case of ZnTe. Nano Letters, 2014, 14, 1877-1883.	9.1	26
39	Optical properties of single ZnTe nanowires grown at low temperature. Applied Physics Letters, 2013, 103, .	3.3	20
40	Growth of AlGaIn/ZnSe/CdSe nanowires for quantum dot luminescence. Journal of Crystal Growth, 2013, 378, 233-237.	1.5	7
41	Terahertz absorbing AlGaIn/GaN multi-quantum-wells: Demonstration of a robust 4-layer design. Applied Physics Letters, 2013, 103, 091108.	3.3	27
42	Exciton-phonon coupling efficiency in CdSe quantum dots embedded in ZnSe nanowires. Physical Review B, 2012, 85, .	3.2	9
43	Ultrafast Room Temperature Single-Photon Source from Nanowire-Quantum Dots. Nano Letters, 2012, 12, 2977-2981.	9.1	70
44	Towards vertical coupling of CdTe/ZnTe quantum dots formed by a high temperature tellurium induced process. Journal of Crystal Growth, 2011, 335, 28-30.	1.5	27
45	Polarity determination in ZnSe nanowires by HAADF STEM. Journal of Physics: Conference Series, 2011, 326, 012044.	0.4	4
46	Strain relaxation in GaN/Al _{0.1} Ga _{0.9} N superlattices for mid-infrared intersubband absorption. Journal of Crystal Growth, 2011, 323, 64-67.	1.5	6
47	Insertion of CdSe quantum dots in ZnSe nanowires: MBE growth and microstructure analysis. Journal of Crystal Growth, 2011, 323, 330-333.	1.5	4
48	Strain relaxation in GaN/Al _x Ga _{1-x} N superlattices grown by plasma-assisted molecular-beam epitaxy. Journal of Applied Physics, 2011, 110, .	2.5	29
49	Insertion of CdSe quantum dots in ZnSe nanowires: Correlation of structural and chemical characterization with photoluminescence. Journal of Applied Physics, 2011, 110, .	2.5	10
50	Epitaxial growth of ZnSe and ZnSe/CdSe nanowires on ZnSe. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 1526-1529.	0.8	12
51	Terahertz intersubband absorption in GaN/AlGaIn step quantum wells. Applied Physics Letters, 2010, 97, .	3.3	87
52	Effects of phosphorus doping on structural and optical properties of silicon nanocrystals in a SiO ₂ matrix. Thin Solid Films, 2009, 517, 5646-5652.	1.8	66
53	Strain effects in GaN/AlN multi-quantum-well structures for infrared optoelectronics. Microelectronics Journal, 2009, 40, 336-338.	2.0	6
54	CdSe quantum dots in ZnSe nanowires as efficient source for single photons up to 220K. Journal of Crystal Growth, 2009, 311, 2123-2127.	1.5	9

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55	Molecular beam epitaxy of semipolar AlN(AlN) and GaN(GaN) on m-sapphire. Journal of Materials Science: Materials in Electronics, 2008, 19, 805-809.	2.2	9
56	Formation of a nanocomposite from plasma enhanced chemical vapour deposition multilayer structures. Journal of Crystal Growth, 2008, 310, 3685-3689.	1.5	13
57	GaN/AlN short-period superlattices for intersubband optoelectronics: A systematic study of their epitaxial growth, design, and performance. Journal of Applied Physics, 2008, 104, 093501.	2.5	165
58	Optical properties of m-plane GaN quantum dots and quantum wires. Journal of Applied Physics, 2008, 104, .	2.5	18
59	Plasma-assisted molecular beam epitaxy growth of GaN nanowires using indium-enhanced diffusion. Applied Physics Letters, 2008, 93, 183109.	3.3	57
60	CdSe quantum dot formation: alternative paths to relaxation of a strained CdSe layer and influence of the capping conditions. Nanotechnology, 2007, 18, 265701.	2.6	9
61	Fabrication and characterization of tin-based nanocrystals. Journal of Applied Physics, 2007, 102, 114304.	2.5	17
62	Plasma-assisted molecular-beam epitaxy of AlN(112 \AA^{-2}) on m sapphire. Applied Physics Letters, 2007, 90, 131909.	3.3	56
63	Molecular beam epitaxy of CdSe epilayers and quantum wells on ZnTe substrate. Applied Surface Science, 2007, 253, 6946-6950.	6.1	20
64	Mechanism of GaN quantum dots capped with AlN: An AFM, electron microscopy, and x-ray anomalous diffraction study. Physical Review B, 2006, 74, .	3.2	25
65	Systematic experimental and theoretical investigation of intersubband absorption in GaN \cdot AlN quantum wells. Physical Review B, 2006, 73, .	3.2	239
66	Undoped and rare-earth doped GaN quantum dots on AlGaIn. Physica Status Solidi (B): Basic Research, 2006, 243, 1472-1475.	1.5	4
67	GaN/AlGaIn superlattices for optoelectronics in the mid-infrared. Physica Status Solidi (B): Basic Research, 2006, 243, 1669-1673.	1.5	0
68	Growth of GaN quantum dots on nonpolar A -plane SiC by molecular-beam epitaxy. Physica Status Solidi (B): Basic Research, 2006, 243, 3968-3971.	1.5	12
69	High-Curie-temperature ferromagnetism in self-organized Ge $_{1-x}$ Mn $_x$ nanocolumns. Nature Materials, 2006, 5, 653-659.	27.5	341
70	Plasma-assisted molecular beam epitaxy of wurtzite GaMnN displaying ferromagnetism assessed by means of X-ray magnetic circular dichroism. Superlattices and Microstructures, 2006, 40, 239-245.	3.1	2
71	Effect of Si doping on GaN/AlN multiple-quantum-well structures for intersubband optoelectronics at telecommunication wavelengths. Superlattices and Microstructures, 2006, 40, 306-312.	3.1	8
72	MBE growth of nitride-based photovoltaic intersubband detectors. Superlattices and Microstructures, 2006, 40, 418-425.	3.1	7

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73	Pre-edge features in X-ray absorption structure of Mn in GaMnN, GaMnAs and GeMn. Journal of Magnetism and Magnetic Materials, 2006, 300, 144-147.	2.3	10
74	Comparison of the structural quality in Ga-face and N-face polarity GaN/AlN multiple-quantum-well structures. Semiconductor Science and Technology, 2006, 21, 612-618.	2.0	33
75	Electrically adjustable intersubband absorption of a GaN ⁺ AlN superlattice grown on a transistorlike structure. Applied Physics Letters, 2006, 89, 101121.	3.3	37
76	Si-doped GaN ⁺ AlN quantum dot superlattices for optoelectronics at telecommunication wavelengths. Journal of Applied Physics, 2006, 100, 044326.	2.5	77
77	High-quality AlN ⁺ GaN-superlattice structures for the fabrication of narrow-band 1.4 μ m photovoltaic intersubband detectors. Applied Physics Letters, 2006, 88, 121112.	3.3	60
78	Observation of hot luminescence and slow inter-sub-band relaxation in Si-doped GaN ⁺ Al _x Ga _{1-x} N (x=0.11, 0.25) multi-quantum-well structures. Journal of Applied Physics, 2006, 99, 093513.	2.5	12
79	Fabrication of self-organized dots of GaN:Mn using plasma-assisted MBE. Journal of Crystal Growth, 2005, 275, e2229-e2232.	1.5	3
80	New method to induce 2D \leftrightarrow 3D transition of strained CdSe/ZnSe layers. Physica E: Low-Dimensional Systems and Nanostructures, 2005, 26, 119-123.	2.7	12
81	GaN quantum dots grown on non-polar a-plane SiC by plasma-assisted molecular beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2341-2344.	0.8	1
82	Optical properties of GaN quantum dots grown on nonpolar (11-20) SiC by molecular-beam epitaxy. Applied Physics Letters, 2005, 86, 171901.	3.3	62
83	Control of the two-dimensional \leftrightarrow three-dimensional transition of self-organized CdSe/ZnSe quantum dots. Nanotechnology, 2005, 16, 1116-1118.	2.6	16
84	Structure and fluctuations of a single floating lipid bilayer. Proceedings of the National Academy of Sciences of the United States of America, 2005, 102, 11639-11644.	7.1	144
85	Ferromagnetic Ga _{1-x} Mn _x N epilayers vs. antiferromagnetic GaMn ₃ N clusters. Europhysics Letters, 2004, 65, 553-559.	2.0	45
86	Plastic strain relaxation of nitride heterostructures. Journal of Applied Physics, 2004, 95, 1127-1133.	2.5	66
87	Recent progress in growth and physics of GaN/AlN quantum dots. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 1445-1450.	0.8	12
88	Growth kinetics of N-face polarity GaN by plasma-assisted molecular-beam epitaxy. Applied Physics Letters, 2004, 84, 3684-3686.	3.3	65
89	Modification of GaN(0001) growth kinetics by Mg doping. Applied Physics Letters, 2004, 84, 2554-2556.	3.3	38
90	Anomalous diffraction in grazing incidence to study the strain induced by GaN quantum dots stacked in an AlN multilayer. Nuclear Instruments & Methods in Physics Research B, 2003, 200, 95-99.	1.4	2

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91	An X-ray and TEM study of inhomogeneous ordering in $\text{Al}_x\text{Ga}_{1-x}\text{N}$ layers grown by MOCVD. <i>Journal of Physics and Chemistry of Solids</i> , 2003, 64, 1653-1656.	4.0	4
92	Lattice dynamics of a strained GaN/AlN quantum well structure. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2003, 17, 557-558.	2.7	2
93	Ordering in undoped hexagonal $\text{Al}_x\text{Ga}_{1-x}\text{N}$ grown on sapphire (0001) with $0.09 < x < 0.247$. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 236, 729-739.	1.5	13
94	Characteristics of AlN growth on vicinal $\text{SiC}(0001)$ substrates by molecular beam epitaxy. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 240, 314-317.	1.5	9
95	Optimization of the growth of $\text{Ga}_{1-x}\text{Mn}_x\text{N}$ epilayers using plasma-assisted MBE. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 240, 443-446.	1.5	20
96	Field-compensated quaternary $\text{InAlGaN}/\text{GaN}$ quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2003, 240, 301-304.	1.5	5
97	Plasma-assisted MBE growth of quaternary InAlGaN quantum well heterostructures with room temperature luminescence. <i>Journal of Crystal Growth</i> , 2003, 251, 476-480.	1.5	31
98	Swelling of Phospholipid Floating Bilayers: The Effect of Chain Length. <i>Langmuir</i> , 2003, 19, 7695-7702.	3.5	45
99	Molecular-beam epitaxial growth and characterization of quaternary III-nitride compounds. <i>Journal of Applied Physics</i> , 2003, 94, 3121-3127.	2.5	60
100	Surfactant effect of In for AlGaIn growth by plasma-assisted molecular beam epitaxy. <i>Journal of Applied Physics</i> , 2003, 93, 1550-1556.	2.5	77
101	Phonon deformation potentials of wurtzite AlN . <i>Journal of Applied Physics</i> , 2003, 93, 2065-2068.	2.5	93
102	Strong influence of Ga/N flux ratio on Mn incorporation into $\text{Ga}_{1-x}\text{Mn}_x\text{N}$ epilayers grown by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2003, 83, 4580-4582.	3.3	40
103	Intersubband spectroscopy of doped and undoped GaN/AlN quantum wells grown by molecular-beam epitaxy. <i>Applied Physics Letters</i> , 2003, 83, 5196-5198.	3.3	85
104	In incorporation during the growth of quaternary III-nitride compounds by plasma-assisted molecular beam epitaxy. <i>Applied Physics Letters</i> , 2003, 82, 2242-2244.	3.3	31
105	On the driving forces for the vertical alignment in nitride quantum dot multilayers. <i>Europhysics Letters</i> , 2003, 63, 268-274.	2.0	16
106	Structural properties of undoped and doped cubic GaN grown on $\text{SiC}(001)$. <i>Journal of Applied Physics</i> , 2002, 91, 4983-4987.	2.5	38
107	Assessment of AlGaIn Growth by Plasma Assisted MBE Using In as a Surfactant. <i>Physica Status Solidi (B): Basic Research</i> , 2002, 234, 726-729.	1.5	7
108	Investigation of GaN quantum dot stacking in multilayers with X-ray grazing incidence techniques. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2002, 93, 24-27.	3.5	1

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109	Structure and ordering of GaN quantum dot multilayer investigated by X-ray grazing incidence techniques. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2002, 13, 1115-1118.	2.7	2
110	A fluid floating bilayer. <i>Europhysics Letters</i> , 2001, 53, 100-106.	2.0	102
111	Structure and ordering of GaN quantum dot multilayers. <i>Applied Physics Letters</i> , 2001, 79, 1971-1973.	3.3	29
112	Evidence for multiple chemical ordering in AlGaIn grown by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2001, 78, 344-346.	3.3	53
113	Interaction of the third helix of Antennapedia homeodomain and a phospholipid monolayer, studied by ellipsometry and PM-IRRAS at the air-water interface. <i>Biochimica Et Biophysica Acta - Biomembranes</i> , 2000, 1467, 131-143.	2.6	82
114	Interaction of the Third Helix of Antennapedia Homeodomain with a Deposited Phospholipid Bilayer: A Neutron Reflectivity Structural Study. <i>Langmuir</i> , 2000, 16, 4581-4588.	3.5	83
115	Growth of Two-Dimensional Solids in Alcohol Monolayers in the Presence of Soluble Amphiphilic Molecules. <i>Langmuir</i> , 2000, 16, 2306-2310.	3.5	5
116	Adsorbed and free lipid bilayers at the solid-liquid interface. <i>European Physical Journal B</i> , 1999, 8, 583-593.	1.5	174
117	Plant sterols: a neutron diffraction study of sitosterol and stigmasterol in soybean phosphatidylcholine membranes. <i>Biophysical Chemistry</i> , 1998, 75, 45-55.	2.8	21